



#### NPN GENERAL PURPOSE TRANSISTORS

VOLTAGE 45 Volt POWER 330 mW

#### **FEATURES**

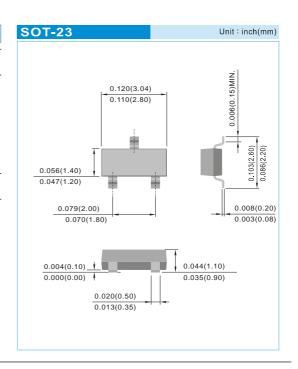
- General purpose amplifier applications
- NPN epitaxial silicon, planar design
- Collector current I<sub>C</sub> = 500mA
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. . (Halogen Free)

#### **MECHANICAL DATA**

- Case: SOT-23, Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounce, 0.0084 gram
- Device Marking: BC817-16:8A

BC817-25 : 8B BC817-40 : 8C





#### **MAXIMUM RATINGS**

PARAMETER		VALUE	UNIT
Collector-Emitter Voltage	VŒ	45	V
Collector-Base Voltage	V <sub>OBO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current - Continuous	Ic	500	mA
Peak Collector Current	I <sub>CM</sub>	1000	mA
Total Power Dissipation ( NOTE )	P <sub>TOT</sub>	330	mW
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	∞

### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Thermal Resistance Junction to Ambient ( NOTE )	$R_{\theta JA}$	375	°C / W
Thermal Resistance Junction to Lead		220	°C / W

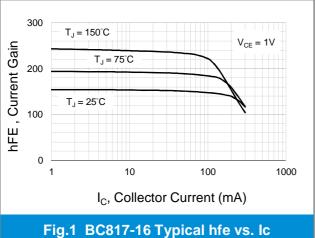
NOTE: Transistor mounted on FR-5 board minimum pad mounting conditions.





### ELECTRICAL CHARACTERISTICS (TJ=25°C,unless otherwise notes)

PARAMETER		SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage ( lc=10mA, lB=0 )		V <sub>(BR)</sub> CEO	45	-	-	V
Collector-Base Breakdown Voltage (V <sub>EB</sub> =0V, lc=10μA)		V <sub>(BR)</sub> CBO	50	-	-	V
Emitter-Base Breakdown Voltage (I <sub>E</sub> =1μA, Ic=0)		V <sub>(BR)</sub> EBO	5	-	-	V
Emitter-Base Cutoff Current (V <sub>EB</sub> =5V)		I <sub>EBO</sub>	=	ı	100	nA
Collector-Base Cutoff Current ( V <sub>CB</sub> =20V, I <sub>E</sub> =0 )	T <sub>J</sub> =25°C T <sub>J</sub> =150°C	l <sub>CBO</sub>	1 1	-	100 5	nΑ μΑ
DC Current Gain ( lc=100mA, V <sub>CE</sub> =1V )  DC Current Gain ( lc=500mA, V <sub>CE</sub> =1V )	BC817-16 BC817-25 BC817-40	h <sub>FE</sub>	100 160 250 40	- - -	250 400 600	-
Collector-Emitter Saturation Voltage ( lc=500mA, l <sub>B</sub> =50mA )	V <sub>CE(SAT)</sub>	-	-	0.7	V	
Base-Emitte Voltage ( lc=500mA, V <sub>CE</sub> =1V )		V <sub>BE(ON)</sub>	-	-	1.2	V
Collector-Base Capacitance (V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz)		C <sub>CBO</sub>	-	7	-	pF
Current Gain-Bandwidth Product ( lc=10mA, V <sub>CE</sub> =5V, f=100MHz )		f <sub>T</sub>	100	-	-	MHz



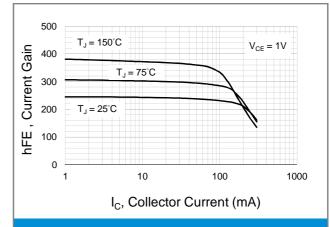


Fig.2 BC817-25 Typical hfe vs. lc

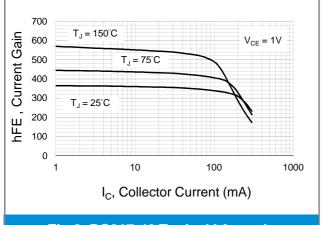
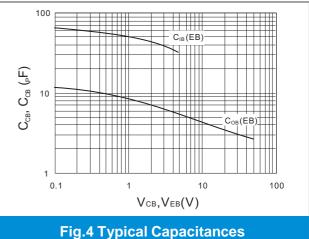


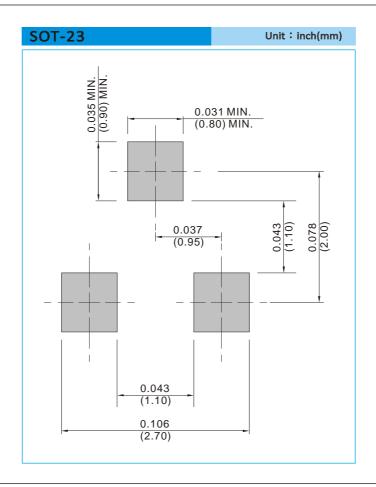
Fig.3 BC817-40 Typical hfe vs. lc







#### **MOUNTING PAD LAYOUT**



### **ORDER INFORMATION**

• Packing information

T/R - 12K per 13" plastic Reel

T/R - 3K per 7" plastic Reel





### Part No\_packing code\_Version

BC817-16\_R1\_00001 BC817-16\_R2\_00001

### For example:



Packing Code XX			Version Code XXXXX			
Packing type	1 <sup>st</sup> Code	Packing size code	2 <sup>nd</sup> Code	HF or RoHS	1 <sup>st</sup> Code	2 <sup>nd</sup> ~5 <sup>th</sup> Code
Tape and Ammunition Box (T/B)	Α	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	В	13"	2			
Tube Packing (T/P)	Т	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			





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